

CLAIMS

1. A method for manufacturing a structure including on a substrate (1) a first metallization level (6) separated from the substrate by a first insulating layer (7) and a second metallization level (9) separated from the first metallization level by a second insulating layer (8), first openings being formed in the first metallization level and in the first insulating layer, and second openings, larger than the first ones being defined in the second metallization level and the second insulating layer, including the steps of:

forming on the substrate a piling of a first insulating layer (7), a first metallization level (6), a second insulating layer (8), and a second metallization level (9),

opening in the second metallization level and in the second insulating layer first windows (11) corresponding to the contour of the first openings and second strip-shaped windows (12), the external contour of which corresponds to the internal contour of the second openings,

forming in a masking layer (20) covering the structure third windows larger than the first windows,

etching the first metallization level in the first windows,

removing the second metallization level (9) under the masking layer to as far as the internal periphery of the second windows,

etching by a chosen distance the first insulating layer (7), and simultaneously removing the second insulating layer (8) within the contour of the second windows, and

removing the masking layer.

2. The method of claim 1, wherein the etchings of the second metallization level, the second insulating layer, and the first metallization level according to the contour of the first windows are vertical anisotropic etchings.

3. The method of claim 1, wherein the first and second metallization levels are made of distinct selectively etchable materials.

5 4. The method of claim 3, wherein the first metallization level is made of niobium and the second metallization level is made of chromium.

5. The method of claim 1, wherein each second opening surrounds a first opening.

10 6. The method of claim 1, wherein each second opening surrounds a group of first openings.